

High-voltage Switching (Audio output amplifier transistor, TV velocity modulation transistor) (160V, 1.5A)

2SC5511

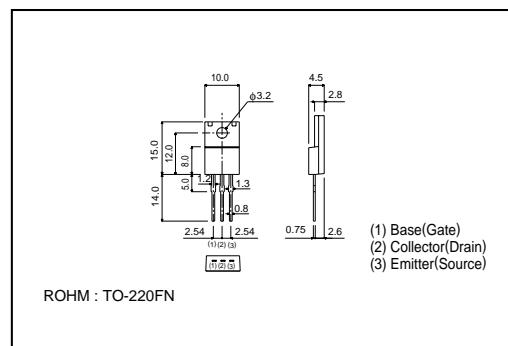
●Features

- 1) Flat DC current gain characteristics.
- 2) High breakdown voltage. ($BV_{CEO} = 160V$)
- 3) High f_T . (Typ. 150MHz)
- 4) Wide SOA (safe operating area).
- 5) Complements the 2SA2005.

●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	160	V
Collector-emitter voltage	V_{CEO}	160	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	1.5	A
Collector power dissipation	P_C	2	W
		20	W ($T_c = 25^\circ C$)
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

●External dimensions (Units : mm)



●Packaging specifications and h_{FE}

Type	2SC5511
Package	TO-220FN
h_{FE}	DE
Code	-
Basic ordering unit	500

●Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV_{CEO}	160	—	—	V	$I_C = 1mA$
Collector-base breakdown voltage	BV_{CBO}	160	—	—	V	$I_C = 50\mu A$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E = 50\mu A$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 160V$
Emitter cutoff current	I_{EBO}	—	—	1	μA	$V_{EB} = 4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	1	V	$I_C/I_B = 1A/0.1A$
DC current transfer ratio	h_{FE}	60	—	200	—	$V_{CE} = 5V, I_C = 0.1A$
Transition frequency	f_T	—	150	—	MHz	$V_{CE} = 10V, I_E = 0.2A, f = 100MHz$
Output capacitance	C_{OB}	—	35	—	pF	$V_{CB} = 10V, I_E = 0A, f = 1MHz$